

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 04-031396

(43)Date of publication of application : 03.02.1992

(51)Int.Cl.

C30B 25/14
C30B 29/40
C30B 29/42
// H01L 21/205

(21)Application number : 02-132514

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(22)Date of filing : 24.05.1990

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(54) GROWTH OF SEMICONDUCTOR CRYSTAL

(57)Abstract:

PURPOSE: To form a monomolecular layer of atomic layer epitaxy in a short time in forming a thin film of semiconductor single crystal from two or more kinds of constituent elements by forming a substantial part of film thickness from low-temperature thermally decomposable raw materials and the rest of the film from raw materials decomposable at a higher temperature.

CONSTITUTION: Raw materials of two or more kinds of constituent elements are alternately fed by an atomic layer epitaxy, a thin film of semiconductor single crystal is grown by each mono-atomic layer and piled to form semiconductor crystal. In the operation, for example, in growing a thin film of single crystal of GaAs, a mono-atomic layer of Ga is formed from a trialkylgallium except trimethylgallium and trimethylgallium and a mono-atomic layer of As is formed from arsine. Consequently, time required for formation of a monomolecular layer by atomic epitaxy is extremely shortened.

LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]